

Abstract**Semiconductor device and method of manufacture**

The present invention relate to a leadframe or flexible printed circuit (FPC) and a method of manufacturing a leadframe or FPC having a GAM value of greater than 2.0. The method comprises subjecting an electrolytically cleaned leadframe or FPC to a microetching step to provide a microetched leadframe or FPC or subjecting an electrolytically cleaned leadframe or FPC to a copper plating process to provide a double copper plated leadframe or FPC. The microetched leadframe or double copper plated leadframe or FPC is then subjected to a bright-deposition nickel plating process, a silver strike electroplating process, a bright silver plating process, and then a silver stripping process to provide a mirror bright silver leadframe or FPC.

Fig. 2